


[Home](#) > [2N7377 \(#23647\)](#)

2N7377 (#23647)

Products

- ▶ [Product Directory](#)
- ▶ [Applications Directory](#)
- ▶ [Parametric Search](#)

Overview

Diagrams

Electrical Rating	Symbol	Min	Typ	Max	Unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$			0.40	V
DC Current Gain	HFE	25.00		75.00	

Maximum Electrical Rating	Symbol	Min	Typ	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	$V_{BR(CBO)}$			400.00	V
Collector Current (dc)	I_C			5.00	A
Collector-Emitter Voltage (Base Open)	V_{CEO}			300.00	V
Emitter-Base Voltage (Collector Open)	V_{EBO}			6.00	V
Power Dissipation, Total	P_T			58.00	W

This part can be found in the following product categories:

- ▶ [Discretes](#) ▶ [Transistors](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [PNP Transistor](#)
- ▶ [Non-Radiation Hardened Devices](#) ▶ [Transistors](#) ▶ [BJT \(BiPolar Junction Transistor\)](#) ▶ [NPN Transistor](#)

Related Links

- [Technical support](#)
- [Sales Contacts](#)
- [Available Stock](#)
- [Sales Contacts](#)
- [RFQ/Samples](#)